

SANYO

No.1405B

2SK436

N-Channel Junction Silicon FET

High-Frequency, Low-Frequency
General-Purpose Amp Applications

Applications

- AM tuner RF amps and low-noise amps.

Features

- Large $|Y_{fs}|$.
- Ultralow noise figure.
- Small C_{rss} .
- Ultrasmall-sized package permitting 2SK436-applied sets to be made small and slim.

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

			unit
Drain-to-Source Voltage	V_{DS}	15	V
Gate-to-Drain Voltage	V_{GDS}	-15	V
Gate Current	I_G	10	mA
Drain Current	I_D	20	mA
Allowable Power Dissipation	P_D	150	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

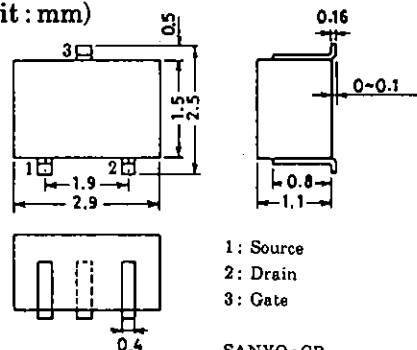
			min	typ	max	unit
G-D Breakdown Voltage	$V_{(BR)GDS}$	$I_G = -10\mu\text{A}, V_{DS} = 0$	-15			V
Gate Cutoff Current	I_{GSS}	$V_{GS} = -10\text{V}, V_{DS} = 0$			-1.0	nA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 5\text{V}, I_D = 100\mu\text{A}$		-0.5	-1.5	V
Drain Current	I_{DSS}	$V_{DS} = 5\text{V}, V_{GS} = 0$	1.2*		12.0*	mA
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 5\text{V}, V_{GS} = 0, f = 1\text{kHz}$	8.0	17		mS
Input Capacitance	C_{iss}	$V_{DS} = 5\text{V}, V_{GS} = 0, f = 1\text{MHz}$		7.0		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = 5\text{V}, V_{GS} = 0, f = 1\text{MHz}$		2.0		pF
Noise Figure	NF	$V_{DS} = 5\text{V}, I_D = 1\text{mA}, R_g = 1\text{k}\Omega, f = 1\text{kHz}$		1.5		dB

* : The 2SK436 is classified by I_{DSS} as follows : (unit : mA)

1.2	17	2.1	1.7	18	3.0	2.5	19	4.2
3.5	20	6.0	5.0	21	8.5	7.3	22	12.0

Note) Marking : A

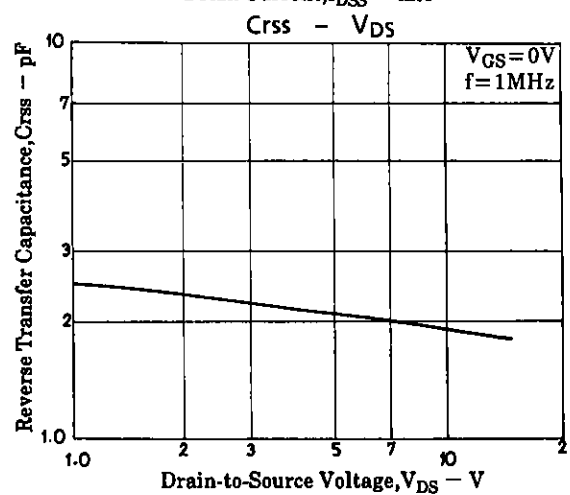
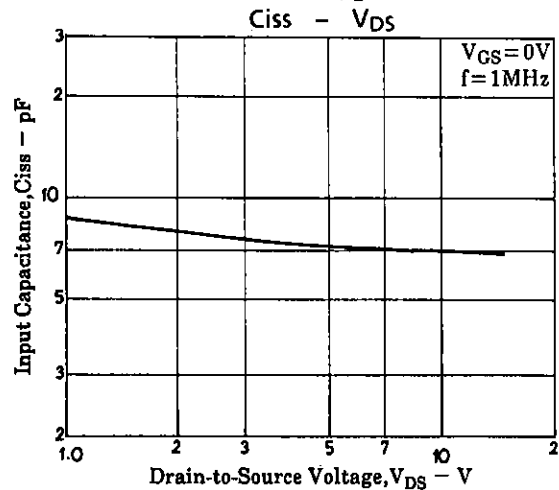
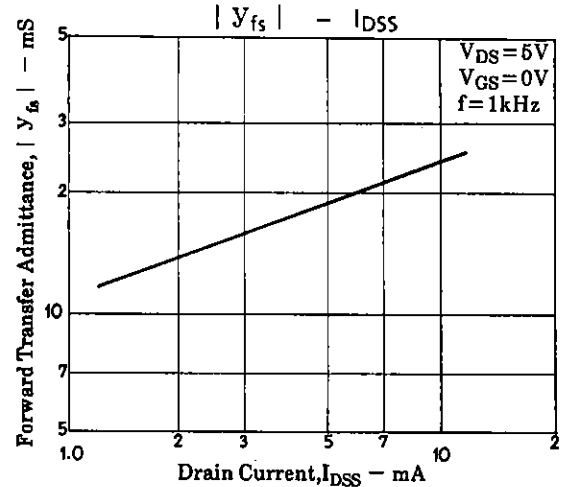
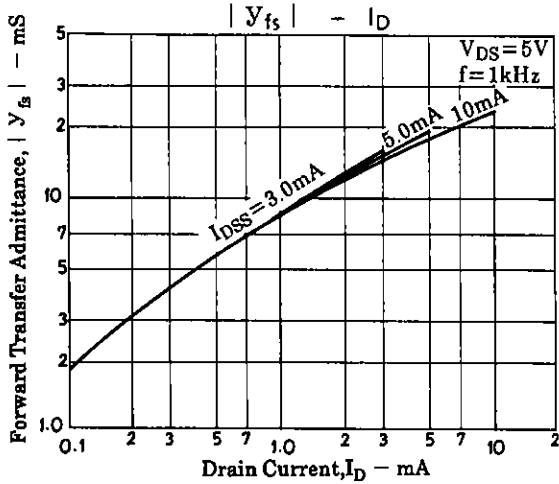
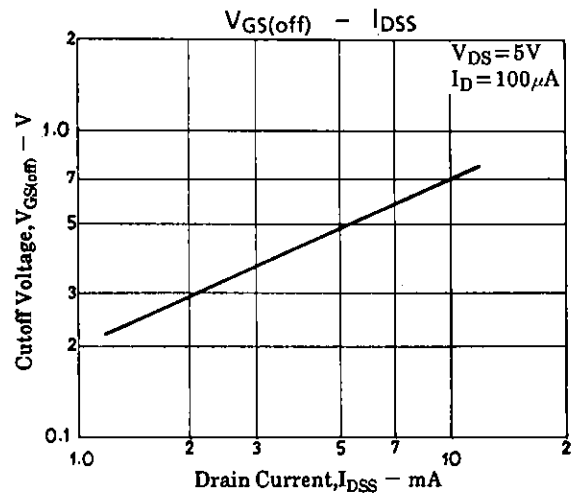
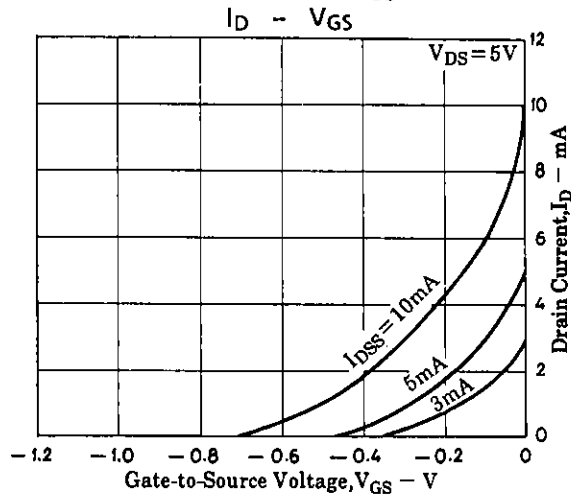
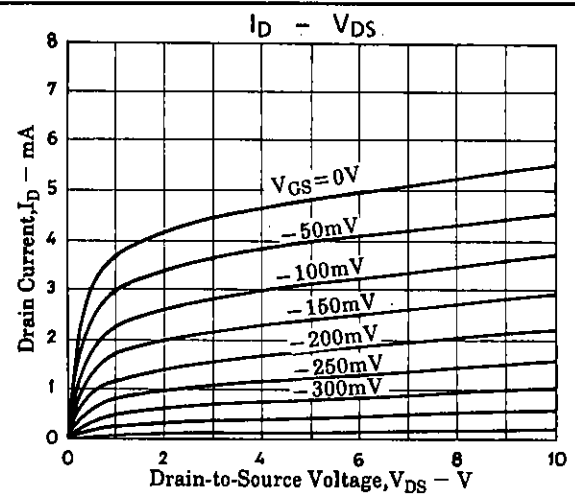
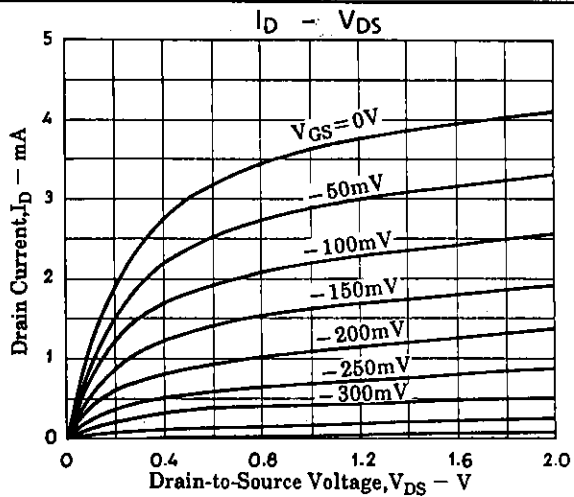
I_{DSS} rank : 17, 18, 19, 20, 21, 22

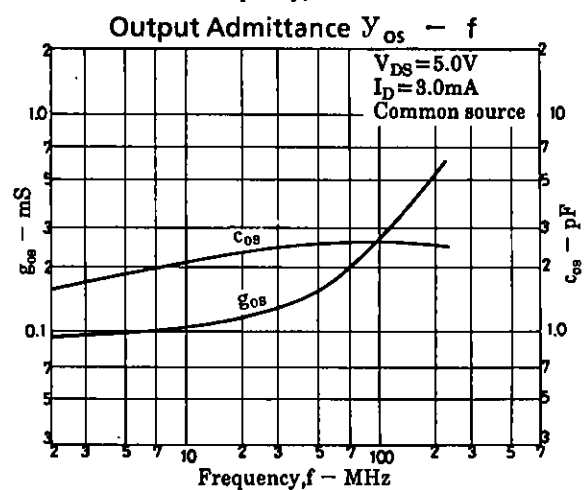
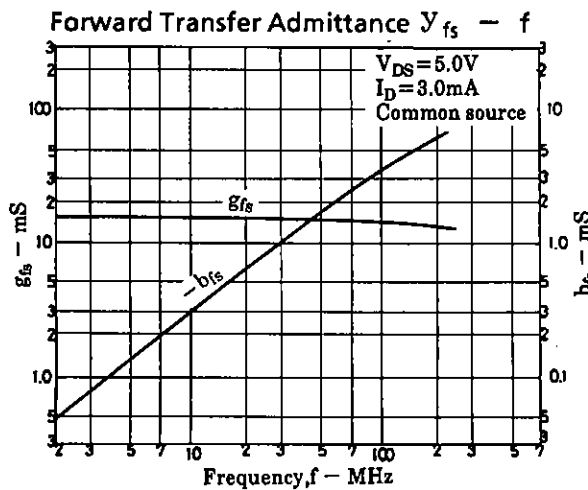
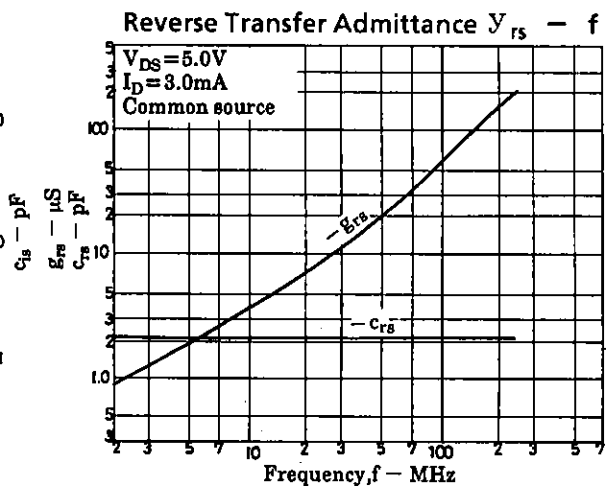
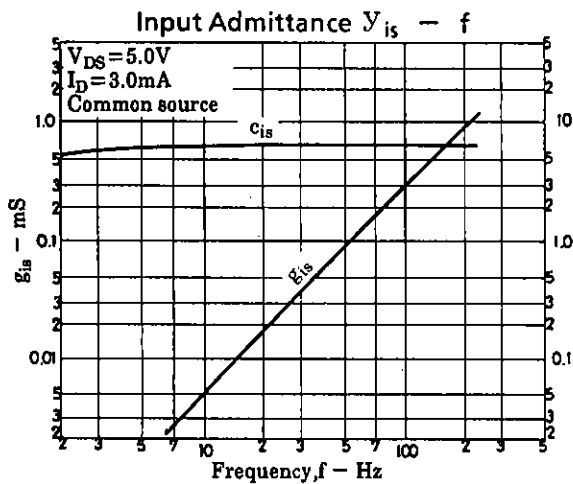
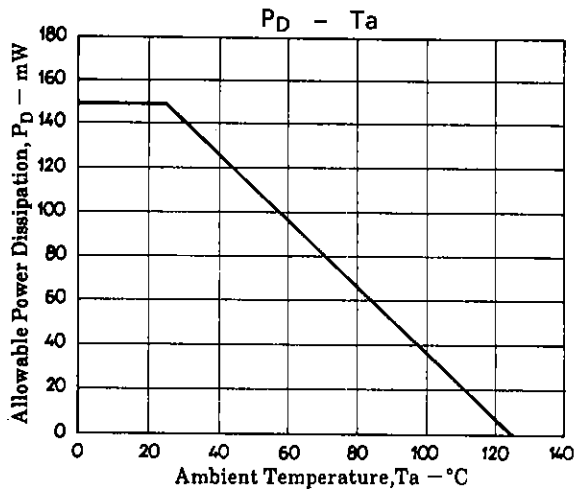
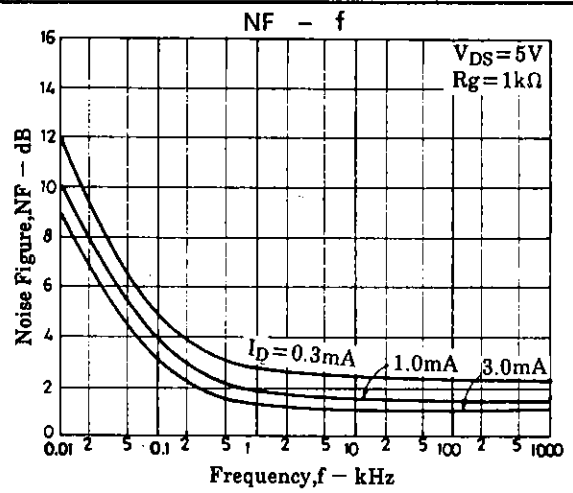
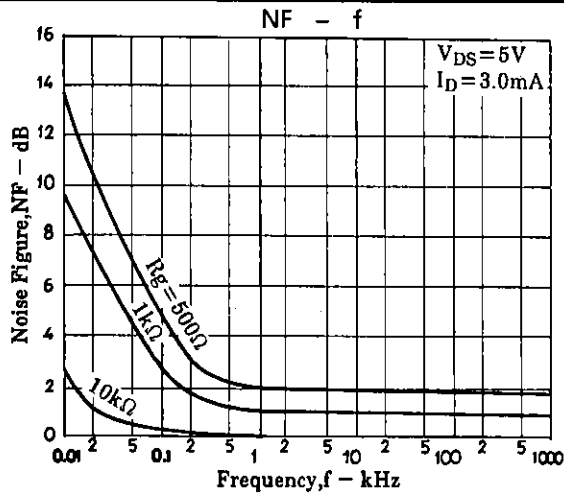
Package Dimensions 2050A
(unit : mm)

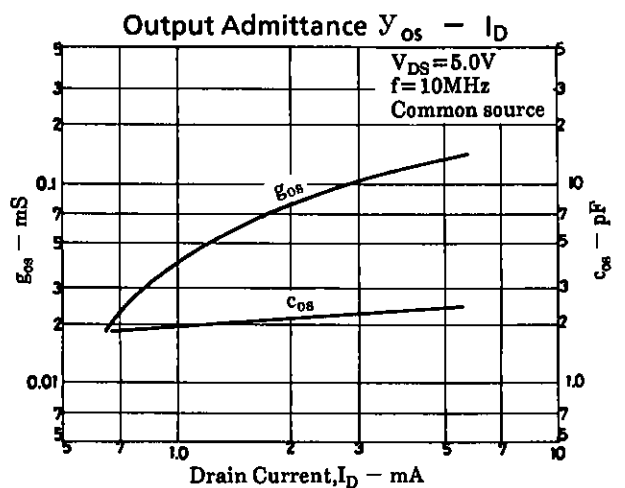
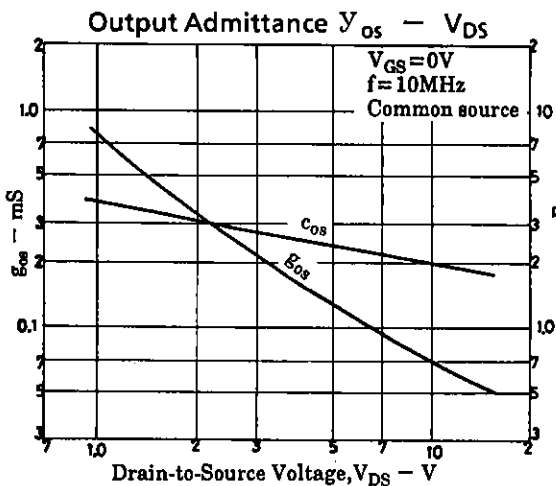
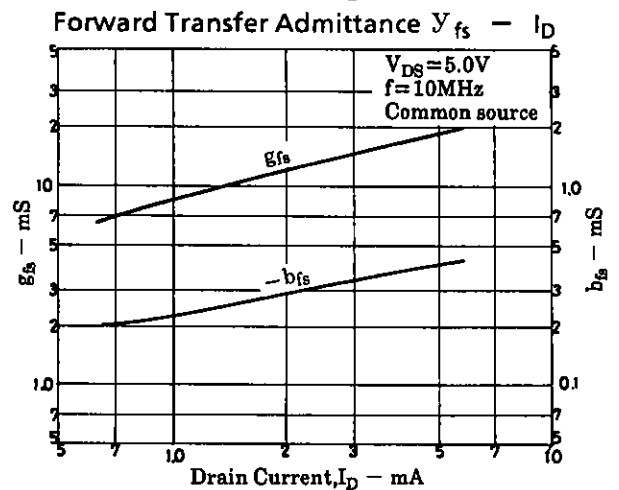
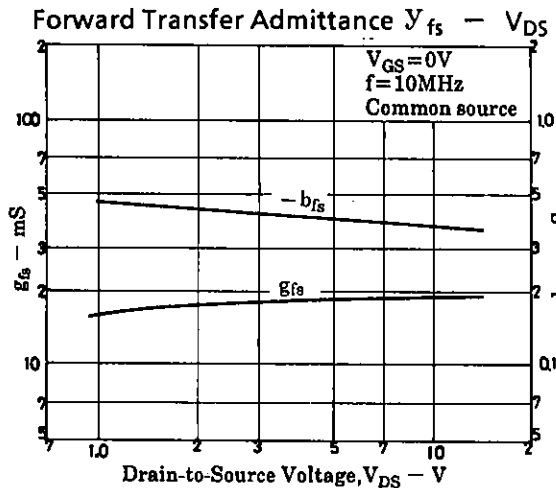
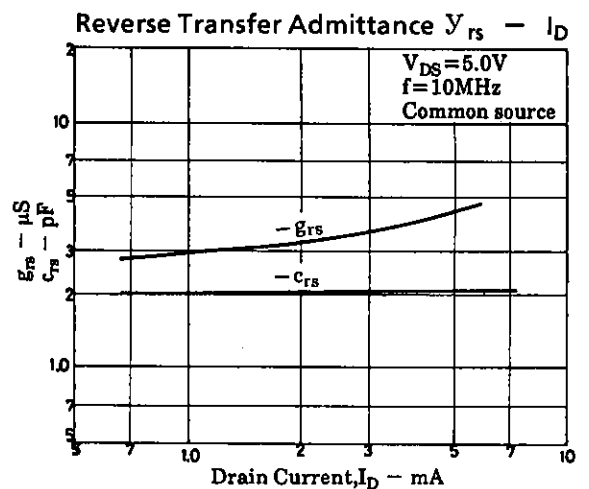
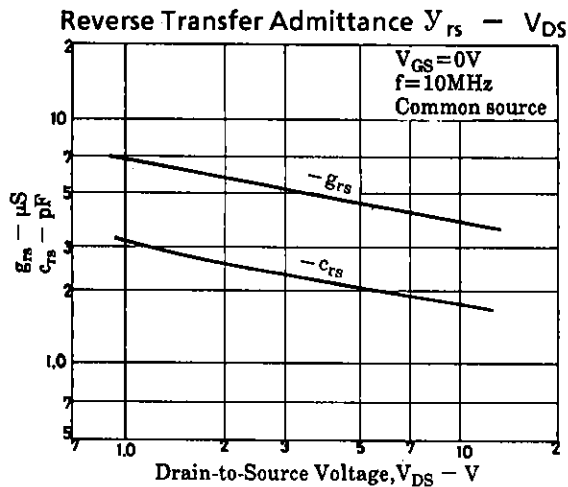
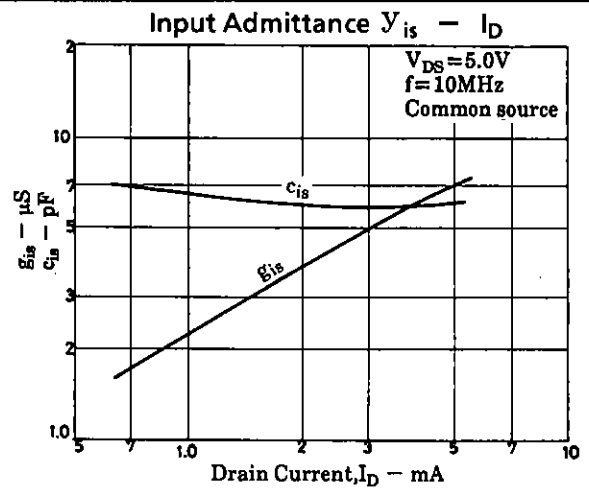
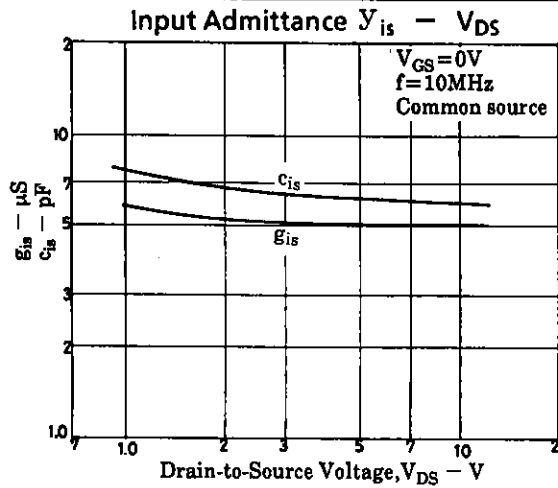
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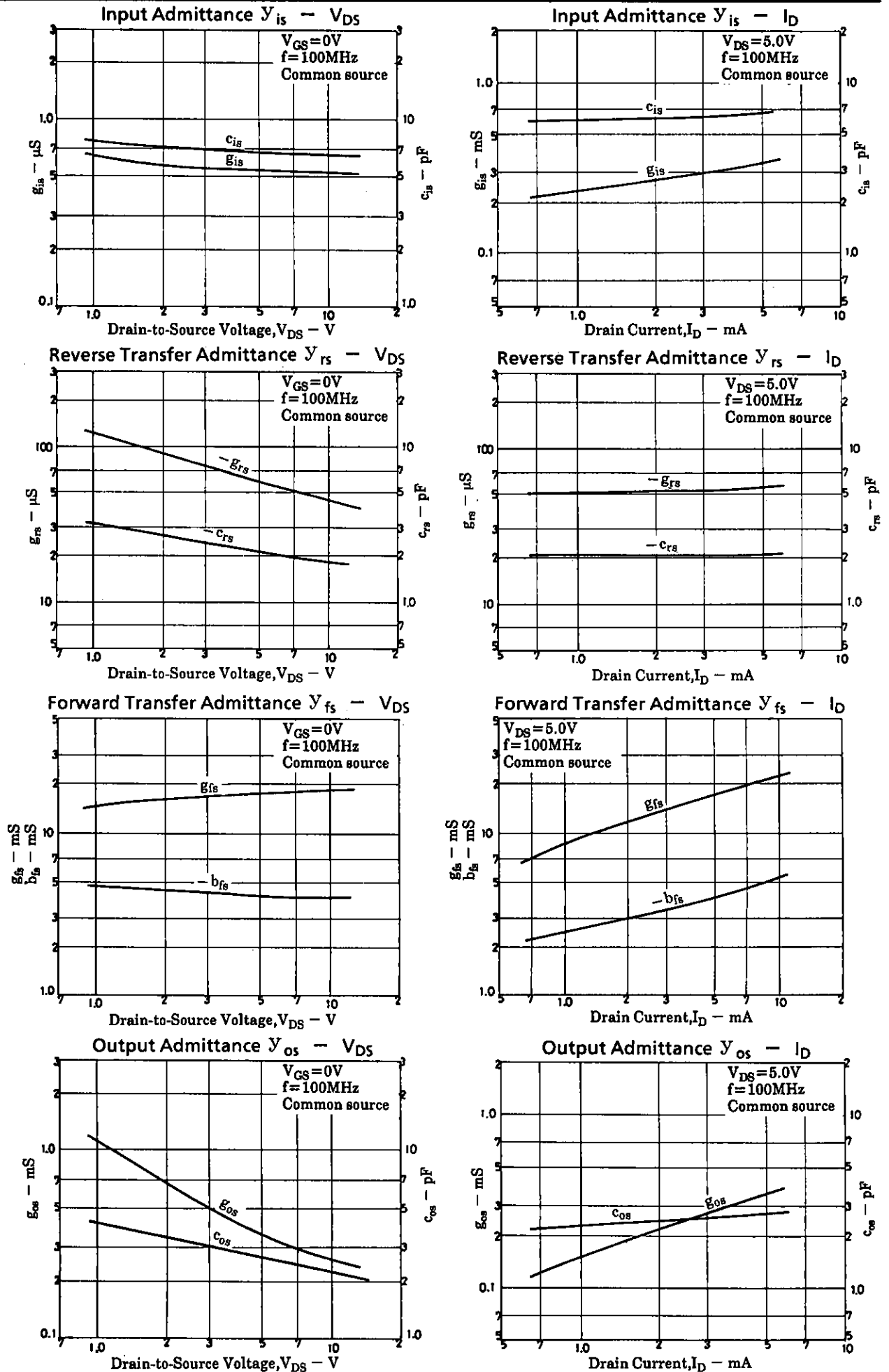
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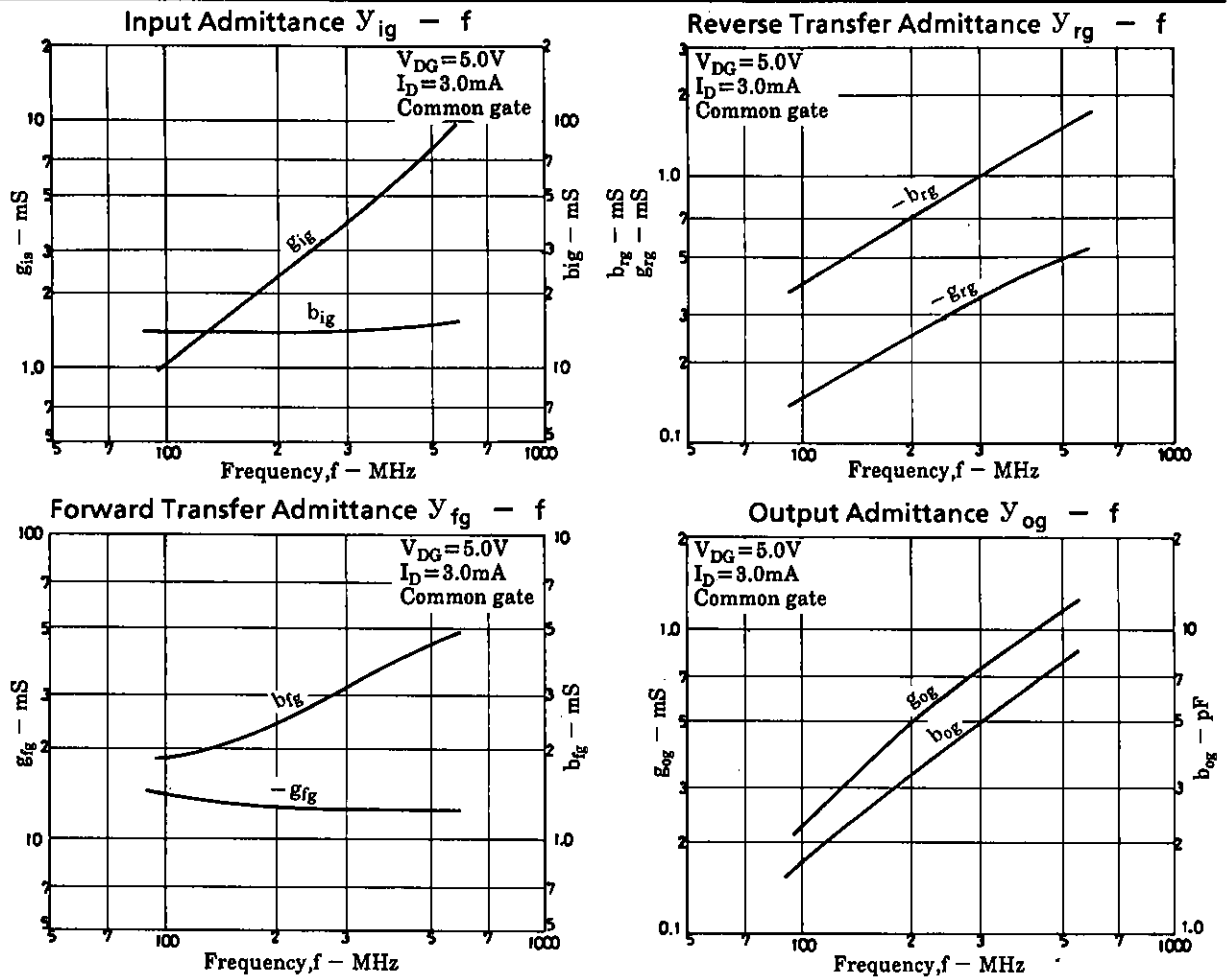
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